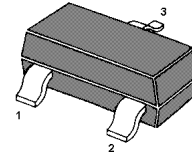
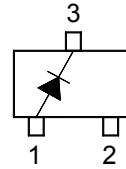


SDB721

Silicon Epitaxial Planar Schottky Barrier Diode

For small current rectification and switching applications



Marking Code: **M1M**
SOT-23 Plastic Package

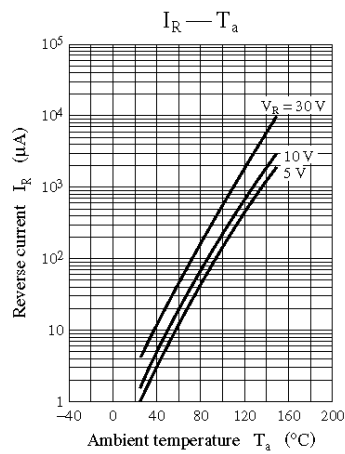
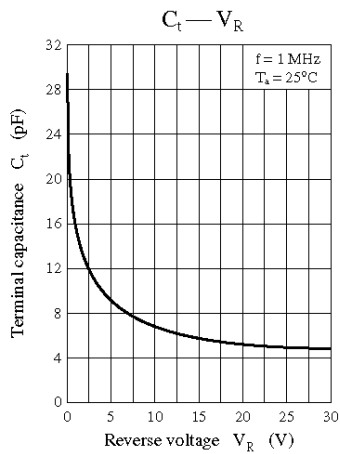
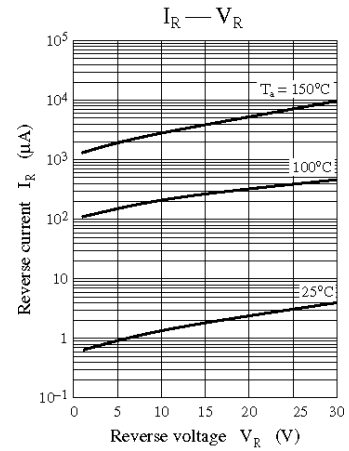
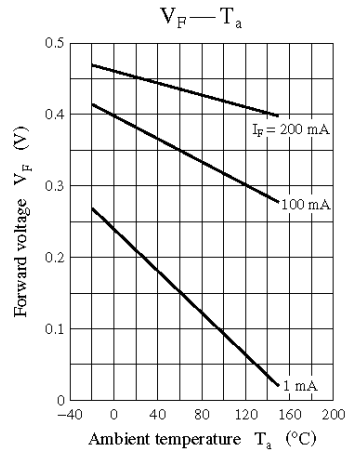
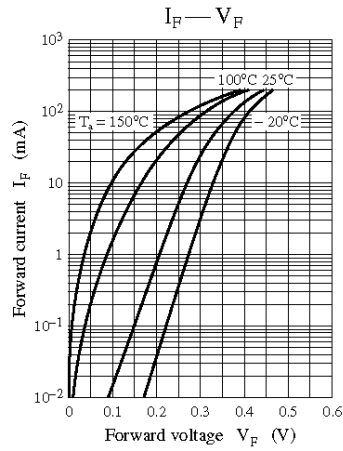
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Average Forward Current	$I_{F(AV)}$	200	mA
Peak Forward Current	I_{FM}	300	mA
Non-repetitive Peak Forward Surge Current (10 ms)	I_{FSM}	1	A
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 200\text{ mA}$	V_F	-	0.55	V
Reverse Current at $V_R = 30\text{ V}$	I_R	-	50	μA
Terminal Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_T	30	-	pF
Reverse Recovery Time at $I_F = I_R = 100\text{ mA}$, $I_{rr} = 10\text{ mA}$, $R_L = 100\ \Omega$	t_{rr}	3	-	ns

TOP DYNAMIC



TOP DYNAMIC